

Configurable Resistive Switching between Memory and Protein-Based Devices

Advanced Functional Materials

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Bidirectional threshold switching in engineered multilayer (Cu ₂ O/Ag:Cu ₂ O/Cu ₂ O) stack for cross-point selector application. Applied Physics Letters, 2015, 107, .	3.3	41
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4	Alcohol-Mediated Resistance-Switching Behavior in Metal-Organic Framework-Based Electronic Devices. Angewandte Chemie, 2016, 128, 9030-9034.	2.0	19
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6	Alcohol-Mediated Resistance-Switching Behavior in Metal-Organic Framework-Based Electronic Devices. Angewandte Chemie - International Edition, 2016, 55, 8884-8888.	13.8	72
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